

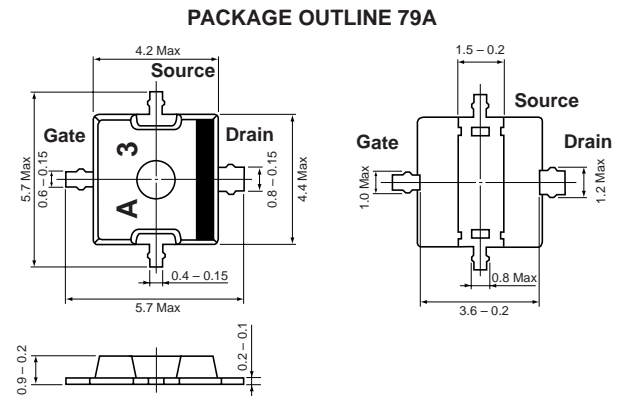
### FEATURES

- **LOW COST PLASTIC SURFACE MOUNT PACKAGE**
- **HIGH OUTPUT POWER:** +35.5 dBm TYP
- **HIGH LINEAR GAIN:** 16 dB TYP @ 915 MHz
- **HIGH POWER ADDED EFFICIENCY:** 65% TYP @  $V_{DS} = 3.2$  V,  $f = 915$  MHz
- **SINGLE SUPPLY:** 2.8 to 6.0 V
- **CLASS AB OPERATION**
- **SURFACE MOUNT PACKAGE:** 5.7x5.7x1.1 mm MAX

### DESCRIPTION

NEC's NE5520379A is an N-Channel silicon power MOSFET specially designed as the transmission power amplifier for 3.2 V GSM900 handsets. Die are manufactured using NEC's NEWMOS technology (NEC's 0.6  $\mu$ m WSi gate lateral MOSFET) and housed in a surface mount package. This device can deliver 35.5 dBm output power at 915 MHz and 3.2 V, or 34.6 dBm output power at 2.8 V by varying the gate voltage as a power control function.

### OUTLINE DIMENSIONS (Units in mm)



### APPLICATIONS

- **DIGITAL CELLULAR PHONES:**  
3.2 V GSM900/DCS 1800 Dual Band Handsets
- **OTHERS:**  
Two-Way Pagers  
Retail Business Radio  
Special Mobile Radio  
Short Range Wireless

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )

PART NUMBER				NE5520379A			TEST CONDITIONS
PACKAGE OUTLINE				79A			
Functional Characteristics	SYMBOLS	CHARACTERISTICS	UNITS	MIN	TYP	MAX	$f = 915$ MHz, $V_{DS} = 3.2$ V, $V_{GS} = 2.5$ V (RF OFF) Duty Cycle $\leq 50\%$ , $T_{on} \leq 1$ s (NOTE 1)
	$P_{OUT}$	Output Power	dBm		35.5		
	GL	Linear Gain (at $P_{IN} = +10$ dBm)	dB		16.0		
	$\eta_D$	Drain Efficiency	%		68		
	$\eta_{ADD}$	Power Added Efficiency	%		65		
	$I_D$	Operating Drain Current	A		1.0		
	$P_{OUT}$	Output Power	dBm	31.0	33.0		
	GL	Linear Gain (at $P_{IN} = +10$ dBm)	dB		8.5		
	$I_D$	Operating Drain Current	mA		750		
	$\eta_D$	Drain Efficiency	%	29	38		
$\eta_{ADD}$	Power Added Efficiency	%		35			
Electrical DC Characteristics	$I_{GSS}$	Gate-to-Source Leakage Current	nA			100	$V_{GSS} = 5.0$ V
	$I_{DSS}$	Drain-to-Source Leakage Current	nA			100	$V_{DSS} = 6.0$ V
	$V_{TH}$	Gate Threshold Voltage	V	1.0	1.35	2.0	$V_{DS} = 3.5$ V, $I_{DS} = 1$ mA
	$g_m$	Transconductance	S		2.5		$V_{DS} = 3.5$ V, $I_{DS1} = 0.8$ A, $I_{DS2} = 1.0$ A
	$R_{DS(ON)}$	Drain-to-Source On Resistance	$\Omega$		0.12	0.15	$V_{GS} = 6.0$ V, $V_{DS} = 0.5$ V
	$BV_{DSS}$	Drain-to-Source Breakdown Voltage	V	15	20		$I_{BSS} = 10$ $\mu$ A
	RTH	Thermal Resistance	$^\circ\text{C/W}$			5	Channel-to-Case

Note:

- DC performance is tested 100%. Several samples per wafer are tested for RF performance. Wafer rejection criteria for standard devices is 1 reject for several samples.

**ABSOLUTE MAXIMUM RATINGS<sup>1</sup>** (T<sub>A</sub> = 25 °C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V <sub>DS</sub>	Drain to Source Voltage	V	15.0
V <sub>GS</sub>	Gate to Source Voltage	V	5.0
I <sub>D</sub>	Drain Current	A	1.5
I <sub>D</sub>	Drain Current (Pulse Test) <sup>2</sup>	A	3.0
P <sub>T</sub>	Total Power Dissipation	W	20
T <sub>CH</sub>	Channel Temperature	°C	125
T <sub>STG</sub>	Storage Temperature	°C	-65 to +125

Note:

1. Operation in excess of any one of these parameters may result in permanent damage.
2. Duty Cycle ≤ 50%, Ton ≤ 1 s.

**RECOMMENDED OPERATING LIMITS**

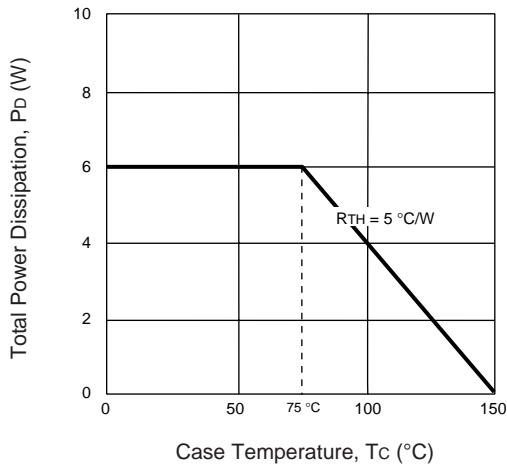
SYMBOLS	PARAMETERS	UNITS	TYP	MAX
V <sub>DS</sub>	Drain to Source Voltage	V	3.2	6.0
V <sub>GS</sub>	Gate to Source Voltage	V	2.5	3.5
I <sub>DS</sub>	Drain Current (Pulse Test)	A	1.75	2.0
P <sub>IN</sub>	Input Power	dBm	25	26

**ORDERING INFORMATION**

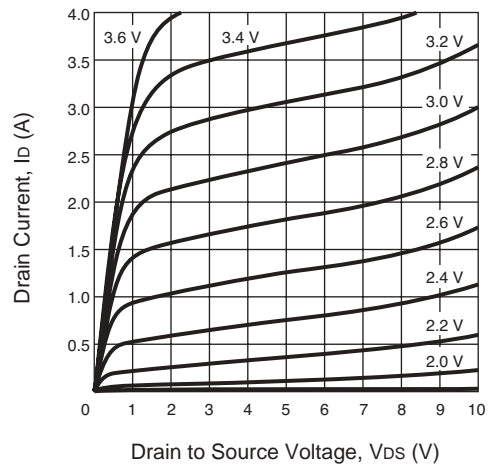
PART NUMBER	QTY
NE5520379A-T1A	<ul style="list-style-type: none"> <li>• 12 mm wide embossed taping.</li> <li>• Gate pin faces the perforation side of the tape.</li> <li>• 5 kpcs/Reel</li> </ul>

**TYPICAL PERFORMANCE CURVES** (T<sub>A</sub> = 25°C)

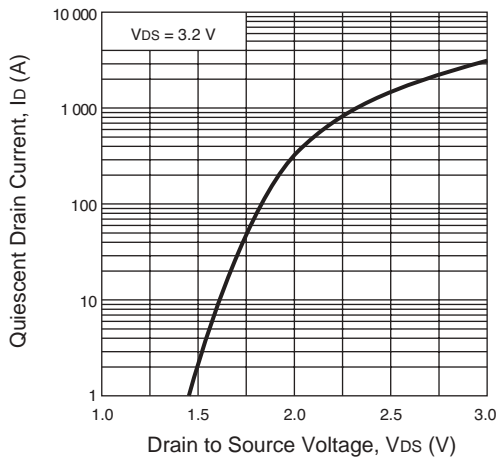
**TOTAL POWER DISSIPATION vs. CASE TEMPERATURE**



**DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE**

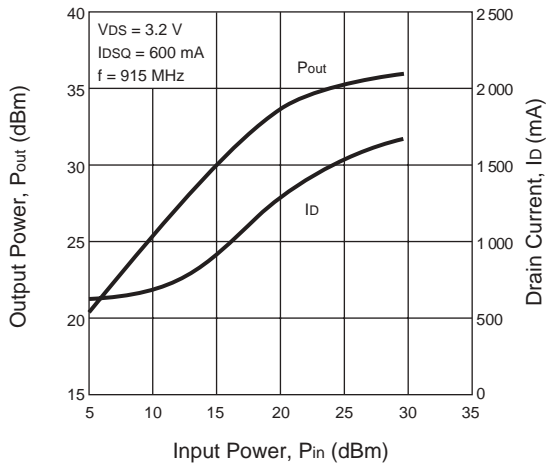


**QUIESCENT DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE**

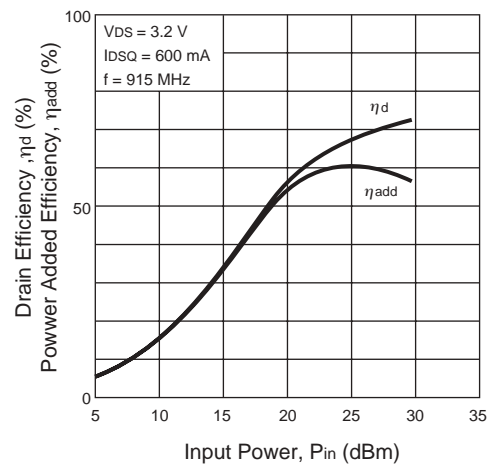


## TYPICAL PERFORMANCE CURVES ( $T_A = 25^\circ\text{C}$ )

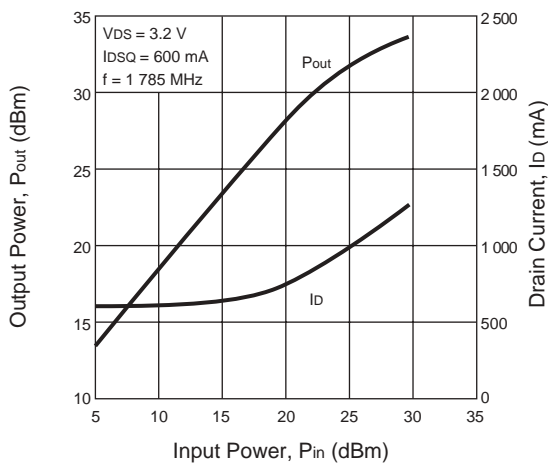
**OUTPUT POWER, DRAIN CURRENT  
vs. INPUT POWER**



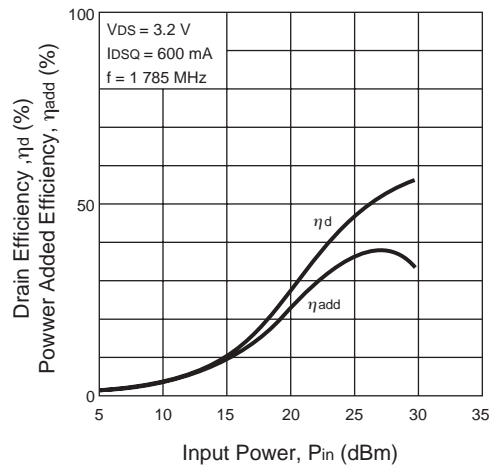
**DRAIN EFFICIENCY, POWER ADDED  
EFFICIENCY vs. INPUT POWER**



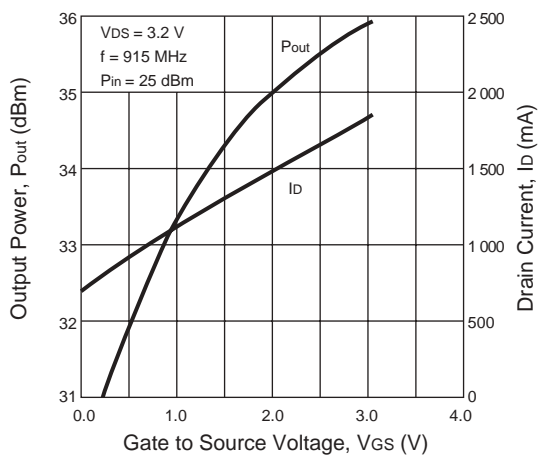
**OUTPUT POWER, DRAIN CURRENT  
vs. INPUT POWER**



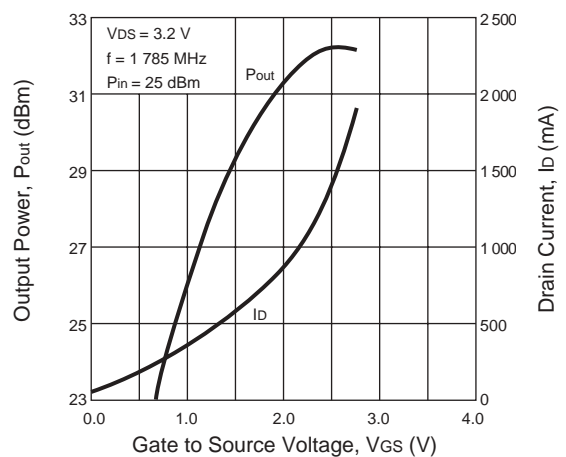
**DRAIN EFFICIENCY, POWER ADDED  
EFFICIENCY vs. INPUT POWER**



**OUTPUT POWER, DRAIN CURRENT  
vs. GATE TO SOURCE VOLTAGE**

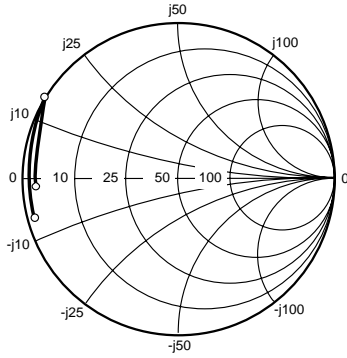


**OUTPUT POWER, DRAIN CURRENT  
vs. GATE TO SOURCE VOLTAGE**

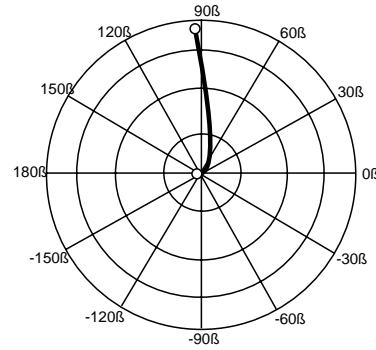


**TYPICAL SCATTERING PARAMETERS** (TA = 25°C)

Note: This file and many other s-parameter files can be downloaded from [www.cel.com](http://www.cel.com)



**Coordinates in Ohms**  
**Frequency in GHz**  
**Vd = 2.4 V, Id = 300 mA**



**NE5520379A**

**Vd = 2.4 V, Id = 300 mA**

FREQUENCY GHz	S11		S21		S12		S22		K	MAG <sup>1</sup> (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		
0.10	0.91	-166.00	4.96	91.46	0.02	2.83	0.87	-177.51	0.12	24.77
0.15	0.91	-171.34	3.32	86.63	0.02	-3.69	0.87	-178.85	0.16	22.87
0.20	0.91	-174.19	2.48	82.34	0.02	-4.78	0.87	-179.72	0.24	21.67
0.25	0.91	-176.05	1.98	78.94	0.02	-7.98	0.87	179.68	0.29	20.65
0.30	0.92	-177.47	1.63	75.61	0.02	-9.01	0.87	179.13	0.37	19.83
0.35	0.92	-178.62	1.39	72.51	0.02	-11.04	0.87	178.64	0.44	19.13
0.40	0.92	-179.56	1.20	69.74	0.02	-14.40	0.88	178.26	0.50	18.71
0.45	0.92	179.62	1.06	66.85	0.02	-16.23	0.88	177.80	0.56	18.21
0.50	0.92	178.83	0.94	64.15	0.02	-18.73	0.88	177.43	0.63	17.79
0.55	0.92	178.12	0.85	61.50	0.02	-20.26	0.88	176.97	0.71	17.43
0.60	0.92	177.42	0.77	58.92	0.01	-19.69	0.88	176.61	0.87	17.25
0.65	0.93	176.76	0.70	56.40	0.01	-22.40	0.89	176.14	0.86	16.77
0.70	0.93	176.09	0.64	53.87	0.01	-24.70	0.89	175.63	0.93	16.44
0.75	0.93	175.48	0.59	51.57	0.01	-26.30	0.89	175.27	1.05	14.89
0.80	0.93	174.86	0.54	49.32	0.01	-27.01	0.89	174.81	1.12	13.95
0.85	0.93	174.22	0.50	46.99	0.01	-28.40	0.89	174.31	1.27	12.74
0.90	0.93	173.60	0.47	44.90	0.01	-29.48	0.90	173.93	1.33	12.17
0.95	0.94	173.03	0.44	42.72	0.01	-31.03	0.90	173.42	1.44	11.53
1.00	0.94	172.43	0.41	40.69	0.01	-31.65	0.90	172.99	1.61	10.79
1.20	0.94	170.05	0.32	33.12	0.01	-35.32	0.91	171.08	2.08	8.96
1.30	0.95	168.90	0.28	29.64	0.01	-38.66	0.91	170.17	2.43	8.10
1.40	0.95	167.71	0.25	26.30	0.01	-40.07	0.91	169.12	2.88	7.18
1.50	0.95	166.62	0.23	23.15	0.01	-40.31	0.92	168.10	3.31	6.55
1.60	0.95	165.46	0.21	20.23	0.01	-42.08	0.92	167.21	4.05	5.86
1.70	0.95	164.33	0.19	17.61	0.01	-41.45	0.92	166.35	4.91	5.12
1.80	0.96	163.28	0.17	15.02	0.01	-41.35	0.92	165.39	5.68	4.38
1.90	0.96	162.22	0.16	12.55	0.00	-40.16	0.93	164.37	7.09	3.84
2.00	0.96	161.21	0.14	10.37	0.00	-35.50	0.93	163.55	8.29	3.46
2.10	0.96	160.17	0.13	8.42	0.00	-30.05	0.93	162.80	11.07	2.90
2.20	0.96	159.17	0.12	6.46	0.00	-21.25	0.93	161.93	14.89	2.19
2.30	0.96	158.29	0.11	4.59	0.00	-15.26	0.94	160.98	16.85	1.67
2.40	0.96	157.41	0.11	3.14	0.00	-1.99	0.94	160.15	18.02	1.65
2.50	0.97	156.53	0.10	1.92	0.00	9.51	0.95	159.57	16.22	1.49
2.60	0.97	155.72	0.09	0.69	0.00	17.40	0.95	158.86	18.87	0.98
2.70	0.97	154.92	0.09	-0.82	0.00	49.62	0.95	158.02	17.17	0.60
2.80	0.97	154.17	0.08	-2.13	0.00	54.56	0.95	157.17	17.91	0.80
2.90	0.97	153.44	0.08	-3.31	0.00	75.69	0.96	156.56	11.30	0.89
3.00	0.97	152.77	0.07	-4.03	0.00	84.78	0.96	155.94	12.00	0.68
3.10	0.97	152.20	0.07	-4.64	0.00	91.22	0.97	155.48	7.64	0.86
3.20	0.98	151.52	0.06	-5.69	0.00	89.31	0.97	154.37	6.03	0.83
3.30	0.98	150.94	0.06	-5.93	0.00	94.43	0.98	153.79	4.52	1.47
3.40	0.98	150.36	0.06	-6.52	0.01	93.75	0.98	153.16	3.50	1.69
3.50	0.98	149.78	0.05	-6.88	0.01	93.93	0.98	152.45	3.08	1.43
4.00	0.99	148.45	0.04	-5.44	0.01	93.64	0.99	150.04	1.13	4.11

Note:

1. Gain Calculation:

$$MAG = \frac{|S_{21}|}{|S_{12}|} (K - \sqrt{K^2 - 1})$$

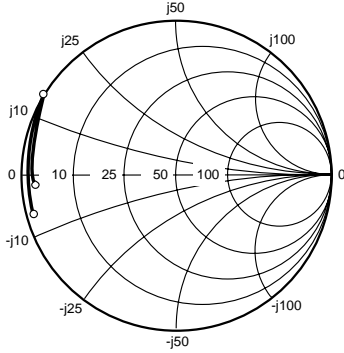
. When  $K \leq 1$ , MAG is undefined and MSG values are used.  $MSG = \frac{|S_{21}|}{|S_{12}|}$ ,  $K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12} S_{21}|}$ ,  $\Delta = S_{11} S_{22} - S_{21} S_{12}$

MAG = Maximum Available Gain

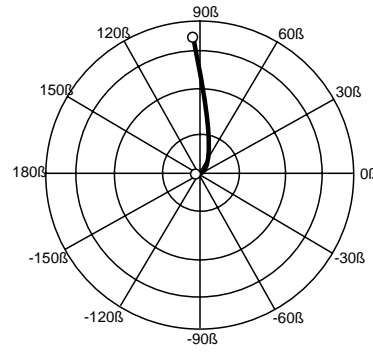
MSG = Maximum Stable Gain

**TYPICAL SCATTERING PARAMETERS** (T<sub>A</sub> = 25°C)

Note: This file and many other s-parameter files can be downloaded from [www.cel.com](http://www.cel.com)



**Coordinates in Ohms  
Frequency in GHz  
V<sub>D</sub> = 3.0 V, I<sub>D</sub> = 600 mA**



**NE5520379A**

**V<sub>D</sub> = 3.0 V, I<sub>D</sub> = 600 mA**

FREQUENCY GHz	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>		K	MAG <sup>1</sup> (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		
0.10	0.93	-166.51	5.08	92.43	0.01	4.88	0.89	-178.46	0.14	26.14
0.15	0.93	-171.79	3.41	88.12	0.01	-2.92	0.89	-179.65	0.15	24.16
0.20	0.93	-174.68	2.54	84.33	0.01	-2.57	0.89	179.54	0.25	23.01
0.25	0.93	-176.58	2.03	81.48	0.01	-2.60	0.89	178.98	0.33	21.95
0.30	0.93	-178.04	1.69	78.54	0.01	-5.09	0.89	178.33	0.39	21.14
0.35	0.93	-179.24	1.44	75.97	0.01	-7.10	0.89	177.89	0.47	20.48
0.40	0.93	179.79	1.25	73.62	0.01	-9.56	0.89	177.44	0.52	20.03
0.45	0.93	178.92	1.11	71.09	0.01	-11.04	0.89	176.93	0.59	19.51
0.50	0.93	178.11	0.99	68.88	0.01	-12.64	0.89	176.63	0.68	19.16
0.55	0.94	177.36	0.89	66.51	0.01	-12.76	0.90	176.06	0.75	18.72
0.60	0.94	176.64	0.81	64.31	0.01	-13.34	0.89	175.72	0.93	18.57
0.65	0.94	175.96	0.75	62.14	0.01	-14.37	0.90	175.29	0.91	18.08
0.70	0.94	175.28	0.69	59.81	0.01	-16.01	0.90	174.68	1.02	17.03
0.75	0.94	174.66	0.63	57.87	0.01	-17.13	0.90	174.42	1.14	15.30
0.80	0.94	174.05	0.59	55.81	0.01	-16.95	0.90	173.89	1.18	14.78
0.85	0.94	173.41	0.55	53.68	0.01	-18.56	0.90	173.39	1.39	13.45
0.90	0.94	172.80	0.51	51.88	0.01	-19.71	0.90	173.13	1.40	13.11
0.95	0.94	172.21	0.48	49.77	0.01	-19.61	0.90	172.51	1.52	12.48
1.00	0.94	171.63	0.45	47.95	0.01	-19.95	0.90	172.16	1.71	11.68
1.10	0.94	170.41	0.40	44.15	0.01	-24.20	0.91	171.11	1.93	10.81
1.20	0.95	169.32	0.36	40.82	0.01	-23.13	0.91	170.30	2.13	10.08
1.30	0.95	168.20	0.32	37.55	0.01	-24.29	0.91	169.48	2.56	9.13
1.40	0.95	167.05	0.29	34.19	0.01	-25.78	0.91	168.40	3.14	8.10
1.50	0.95	166.00	0.27	30.96	0.01	-25.39	0.92	167.30	3.52	7.56
1.60	0.95	164.89	0.24	28.24	0.01	-25.03	0.92	166.57	4.07	7.05
1.70	0.95	163.80	0.22	25.67	0.01	-22.37	0.92	165.86	4.72	6.28
1.80	0.95	162.78	0.20	22.92	0.00	-20.35	0.92	164.91	6.13	5.28
1.90	0.96	161.76	0.19	20.12	0.00	-18.82	0.92	163.74	7.13	4.85
2.00	0.96	160.78	0.18	17.88	0.00	-12.65	0.93	162.96	7.85	4.65
2.10	0.96	159.78	0.16	16.09	0.00	-5.72	0.93	162.54	9.04	4.16
2.20	0.96	158.80	0.15	14.12	0.00	2.28	0.93	161.73	11.69	3.15
2.30	0.96	157.95	0.14	12.01	0.00	9.59	0.93	160.62	12.90	2.58
2.40	0.96	157.10	0.13	10.33	0.00	16.52	0.94	159.68	11.53	2.95
2.50	0.96	156.24	0.12	9.11	0.00	24.13	0.95	159.46	10.27	2.98
2.60	0.96	155.45	0.12	7.63	0.00	38.01	0.94	158.99	11.45	2.19
2.70	0.97	154.66	0.11	5.72	0.00	48.37	0.94	158.00	10.95	1.62
2.80	0.97	153.93	0.10	3.94	0.00	55.62	0.95	156.90	10.04	2.00
2.90	0.97	153.22	0.10	2.73	0.00	64.87	0.96	156.45	7.62	2.62
3.00	0.97	152.55	0.09	1.96	0.00	69.74	0.96	156.03	7.17	2.29
3.10	0.97	152.00	0.09	1.15	0.00	81.95	0.96	155.48	6.39	2.11
3.20	0.97	151.33	0.08	-0.21	0.00	80.85	0.97	154.23	5.03	2.21
3.30	0.98	150.77	0.08	-0.76	0.01	86.32	0.97	153.57	3.62	3.03
3.40	0.98	150.20	0.07	-1.47	0.01	86.22	0.98	153.08	3.20	3.00
3.50	0.98	149.63	0.07	-2.27	0.01	87.98	0.97	152.19	3.09	2.26
4.00	0.99	148.33	0.05	-2.98	0.01	88.38	0.98	149.87	1.37	3.81

Note:

1. Gain Calculation:

$$MAG = \frac{|S_{21}|}{|S_{12}|} (K - \sqrt{K^2 - 1})$$

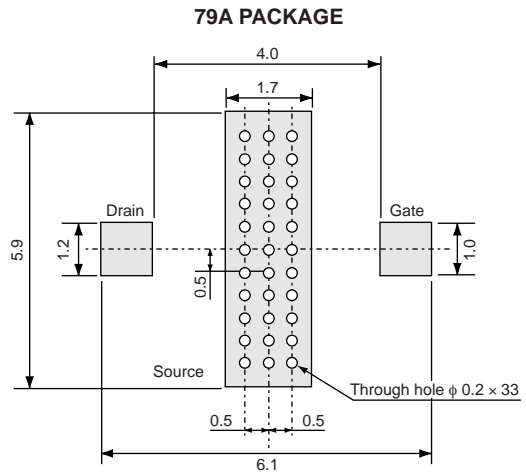
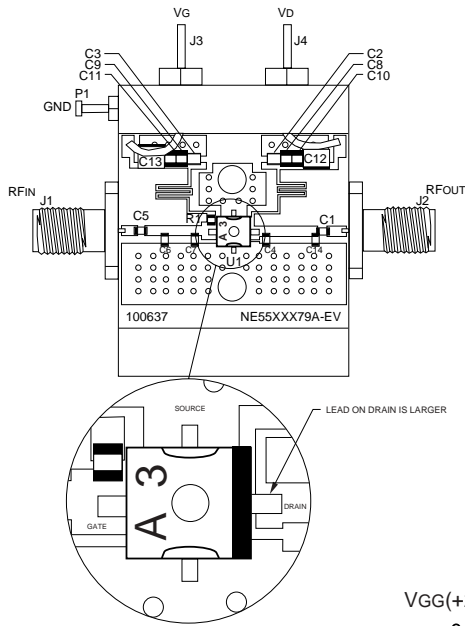
When K ≤ 1, MAG is undefined and MSG values are used.  $MSG = \frac{|S_{21}|}{|S_{12}|}$ ,  $K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12}| |S_{21}|}$ ,  $\Delta = S_{11} S_{22} - S_{21} S_{12}$

MAG = Maximum Available Gain

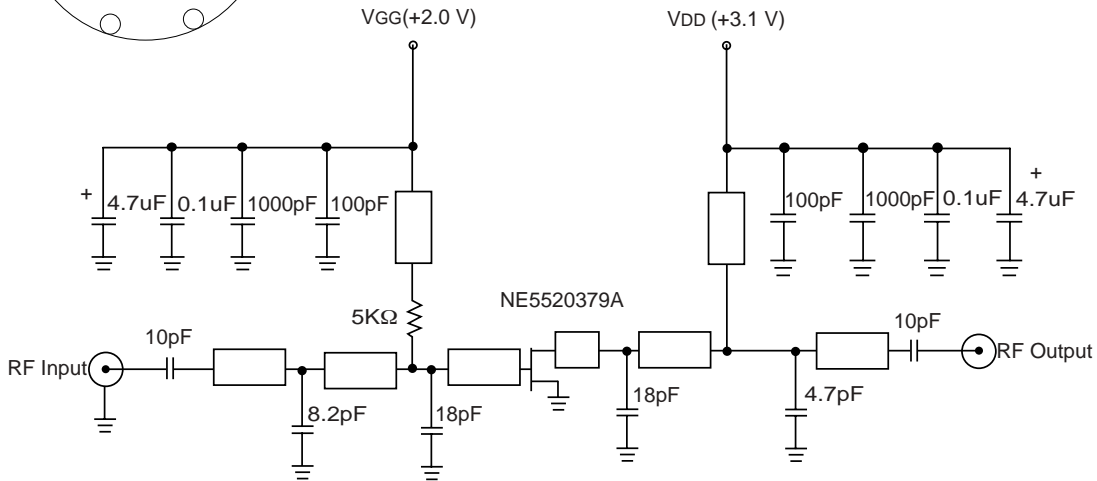
MSG = Maximum Stable Gain

APPLICATION CIRCUIT (900 MHz)

P.C.B. LAYOUT (Units in mm)



Note:  
Use rosin or other material to prevent solder from penetrating through-holes.



NE5520379A PARTS LIST

1	TF-100637		TEST CIRCUIT BLK	16
4			2-56 X 3/16 PHILLIPS PAN HEAD	15
2	MA101J	C2, C3	CASE 1100 pF CAP MURATA	14
1	MCR03J512	R1	0603 5.1K OHMS RESISTOR ROHM	13
2	MCH185A180JK	C4, C7	0603 18 pF CAP ROHM	12
1	MCH185A4R7CK	C14	0603 4.7 pF CAP ROHM	11
2	MCH185A100DK	C1, C5	0603 10 pF CAP ROHM	10
1	MCH185A8R2DK	C6	0603 8.2 pF CAP ROHM	9
2	TAJB475K010R	C12, C13	CASE B 4.7 uF CAP ATC	8
2	GRM40X7R104K025BL	C10, C11	0805 .1 uF CAP MURATA	7
2	GRM40C0G102J050BD	C8, C9	0805 1000 pF CAP MURATA	6
1	NE5520379A	U1	IC NEC, LD-MOS FET	5
1	703401	P1	GROUND LUG CONCORD	4
1	1250-003	J3, J4	FEEDTHRU MURATA	3
2	2052-5636-02	J1, J2	FLANGE MOUNT JACK RECEPTACLE	2
1	FD-100637	PCB	NE5520379A-EVAL FAB. DRAWING	1

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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